



# STPS60150C

## POWER SCHOTTKY RECTIFIER

**Table 1: Main Product Characteristics**

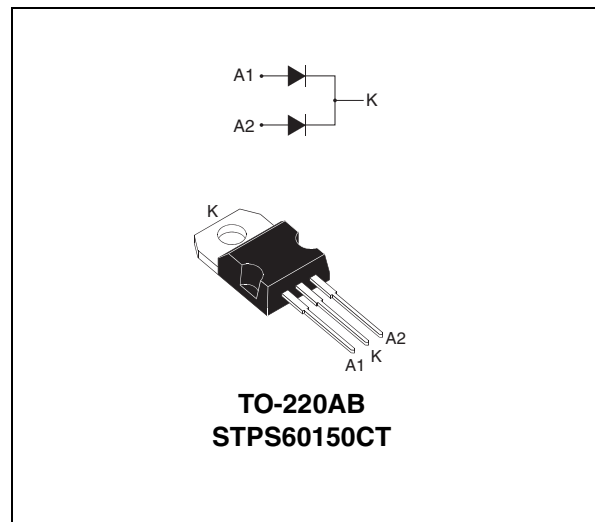
$I_{F(AV)}$	<b>2 x 30 A</b>
$V_{RRM}$	<b>150 V</b>
$T_j$	<b>175°C</b>
$V_F(max)$	<b>0.76 V</b>

### FEATURES AND BENEFITS

- High junction temperature capability
- Low leakage current
- Low thermal resistance
- High frequency operation
- Avalanche specification

### DESCRIPTION

Dual center tab Schottky rectifier suited for High Frequency server and telecom base station SMPS. Packaged in TO-220AB, this device combines high current rating and low volume to enhance both reliability and power density of the application.



**Table 2: Order Codes**

Part Number	Marking
STPS60150CT	STPS60150CT

**Table 3: Absolute Ratings** (limiting values, per diode)

Symbol	Parameter		Value	Unit
$V_{RRM}$	Repetitive peak reverse voltage		150	V
$I_{F(RMS)}$	RMS forward voltage		60	A
$I_{F(AV)}$	Average forward current	$T_c = 150^\circ\text{C}$ $\delta = 0.5$	Per diode 30 Per device 60	A
$I_{FSM}$	Surge non repetitive forward current		$t_p = 10\text{ms}$ sinusoidal	270 A
$P_{ARM}$	Repetitive peak avalanche power		$t_p = 1\mu\text{s}$ $T_j = 25^\circ\text{C}$	17300 W
$T_{stg}$	Storage temperature range		-65 to + 175	°C
$T_j$	Maximum operating junction temperature *		175	°C
dV/dt	Critical rate of rise of reverse voltage		10000	V/ $\mu\text{s}$

\*:  $\frac{dP_{tot}}{dT_j} > \frac{1}{R_{th(j-a)}}$  thermal runaway condition for a diode on its own heatsink

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**Table 4: Thermal Parameters**

Symbol	Parameter		Value	Unit
$R_{th(j-c)}$	Junction to case	Per diode	1.0	$^{\circ}\text{C}/\text{W}$
		Total	0.7	
$R_{th(c)}$	Coupling		0.4	

When the diodes 1 and 2 are used simultaneously:

$$\Delta T_j(\text{diode 1}) = P(\text{diode 1}) \times R_{th(j-c)}(\text{Per diode}) + P(\text{diode 2}) \times R_{th(c)}$$

**Table 5: Static Electrical Characteristics (per diode)**

Symbol	Parameter	Tests conditions		Min.	Typ	Max.	Unit
$I_R^*$	Reverse leakage current	$T_j = 25^{\circ}\text{C}$	$V_R = V_{RRM}$		3	15	$\mu\text{A}$
		$T_j = 125^{\circ}\text{C}$			3	10	mA
$V_F^{**}$	Forward voltage drop	$T_j = 25^{\circ}\text{C}$	$I_F = 30\text{A}$			0.94	V
		$T_j = 125^{\circ}\text{C}$	$I_F = 30\text{A}$		0.72	0.76	
		$T_j = 25^{\circ}\text{C}$	$I_F = 60\text{A}$		0.97	1.05	
		$T_j = 125^{\circ}\text{C}$	$I_F = 60\text{A}$		0.86	0.92	

Pulse test: \*  $t_p = 5 \text{ ms}$ ,  $\delta < 2\%$

\*\*  $t_p = 380 \mu\text{s}$ ,  $\delta < 2\%$

To evaluate the conduction losses use the following equation:  $P = 0.6 \times I_{F(AV)} + 0.0053 I_{F(RMS)}^2$

Figure 1: Average forward power dissipation versus average forward current (per diode)

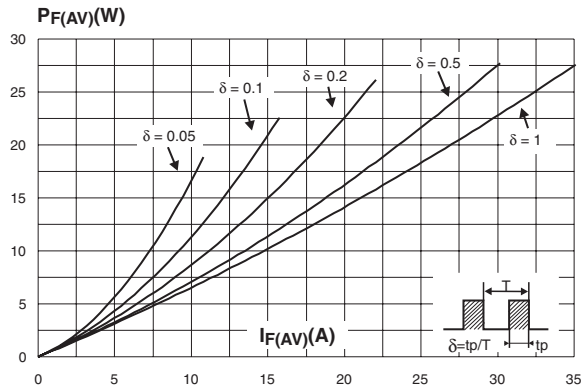


Figure 2: Average forward current versus ambient temperature ( $\delta = 0.5$ , per diode)

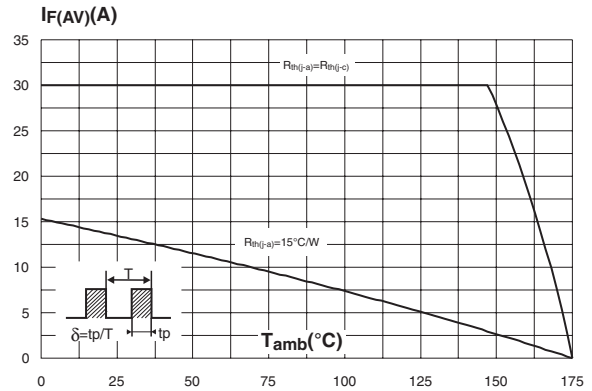


Figure 3: Normalized avalanche power derating versus pulse duration

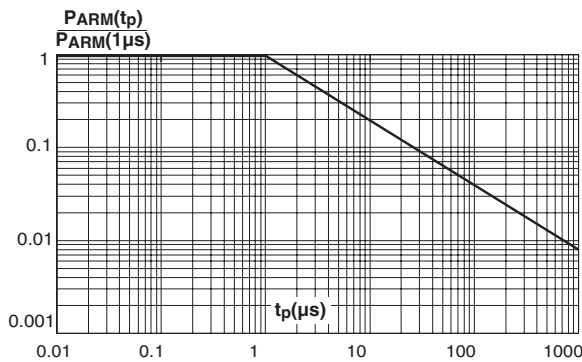


Figure 4: Normalized avalanche power derating versus junction temperature

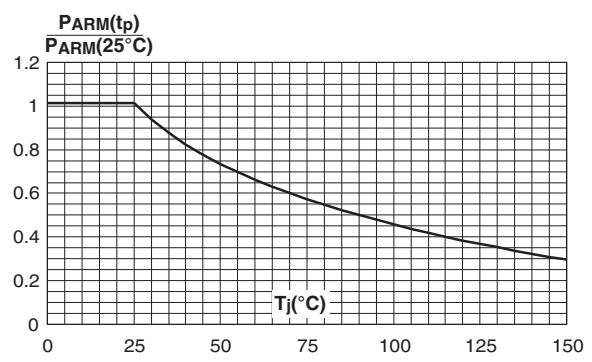


Figure 5: Non repetitive surge peak forward current versus overload duration (maximum values, per diode)

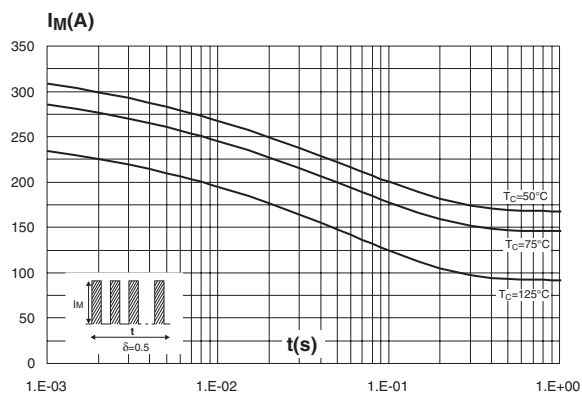
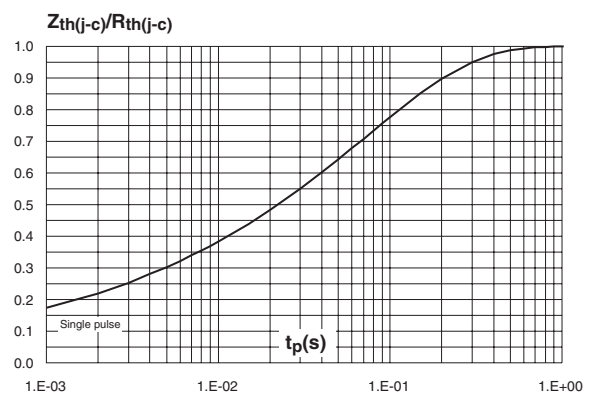
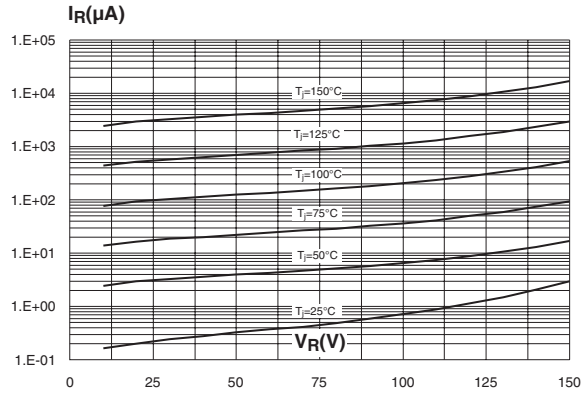


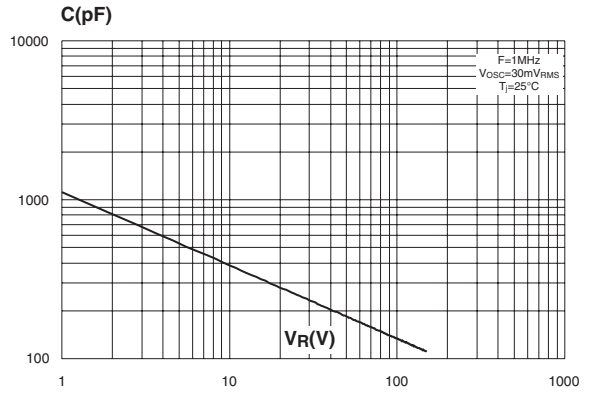
Figure 6: Relative variation of thermal impedance junction to case versus pulse duration (per diode)



**Figure 7: Reverse leakage current versus reverse voltage applied (typical values, per diode)**



**Figure 8: Junction capacitance versus reverse voltage applied (typical values, per diode)**



**Figure 9: Forward voltage drop versus forward current (per diode)**

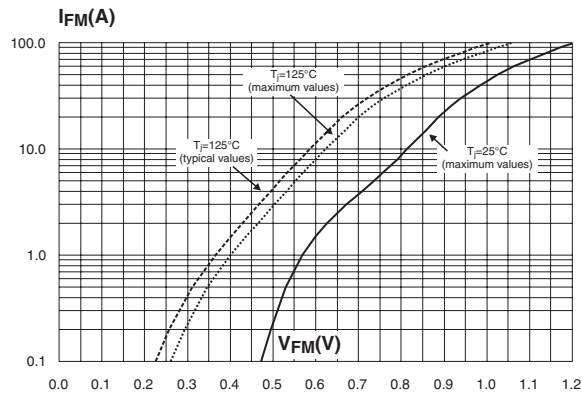


Figure 10: TO-220AB Package Mechanical Data

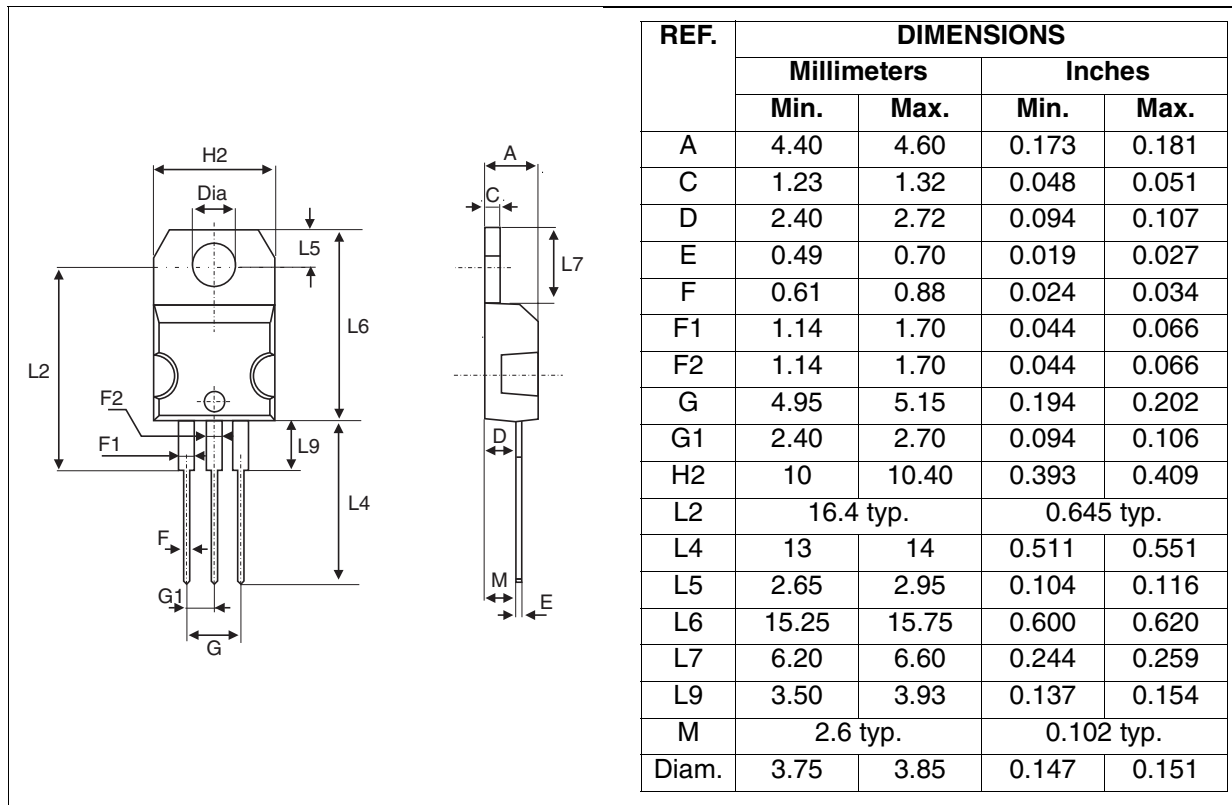


Table 6: Ordering Information

Ordering type	Marking	Package	Weight	Base qty	Delivery mode
STPS60150CT	STPS60150CT	TO-220AB	2.20 g	50	Tube

- Epoxy meets UL94, V0
- Cooling method: by conduction (C)
- Recommended torque value: 0.8 m.N.
- Maximum torque value: 1.0 m.N.

Table 7: Revision History

Date	Revision	Description of Changes
19-Oct-2004	1	First issue.

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